BC857AM,315 Datasheet

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DiGi Electronics Part Number	BC857AM,315-DG
Manufacturer	Nexperia USA Inc.
Manufacturer Product Number	BC857AM,315
Description	TRANS PNP 45V 0.1A SOT883
Detailed Description	Bipolar (BJT) Transistor PNP 45 V 100 mA 100MHz 150 mW Surface Mount SOT-883

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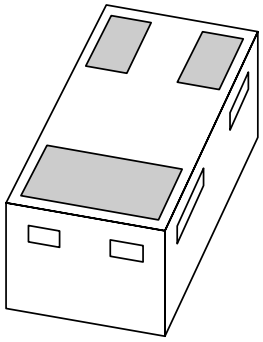
Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
BC857AM,315	Nexperia USA Inc.
Series:	Product Status:
-	Active
Transistor Type:	Current - Collector (Ic) (Max):
PNP	100 mA
Voltage - Collector Emitter Breakdown (Max):	Vce Saturation (Max) @ Ib, Ic:
45 V	400mV @ 5mA, 100mA
Current - Collector Cutoff (Max):	DC Current Gain (hFE) (Min) @ Ic, Vce:
15nA (ICBO)	125 @ 2mA, 5V
Power - Max:	Frequency - Transition:
150 mW	100MHz
Operating Temperature:	Grade:
150°C (TJ)	Automotive
Qualification:	Mounting Type:
AEC-Q101	Surface Mount
Package / Case:	Supplier Device Package:
SC-101, SOT-883	SOT-883
Base Product Number:	
BC857	

Environmental & Export classification

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	
8541.21.0075	

DATA SHEET



BC857M series
PNP general purpose transistors

Product data sheet
Supersedes data of 2003 Jul 15

2004 Mar 10

PNP general purpose transistors BC857M series

FEATURES

- Leadless ultra small plastic package (1 mm × 0.6 mm × 0.5 mm)
- Board space 1.3 × 0.9 mm
- Power dissipation comparable to SOT23.

APPLICATIONS

- General purpose small signal DC
- Low and medium frequency AC applications
- Mobile communications, digital (still) cameras, PDAs, PCMCIA cards.

DESCRIPTION

PNP general purpose transistor in a SOT883 leadless ultra small plastic package.
NPN complement: BC847M series.

MARKING

TYPE NUMBER	MARKING CODE
BC857AM	D1
BC857BM	D2
BC857CM	D3

QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
V_{CEO}	collector-emitter voltage	−45	V
I_C	collector current (DC)	−100	mA
I_{CM}	peak collector current	−200	mA

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector

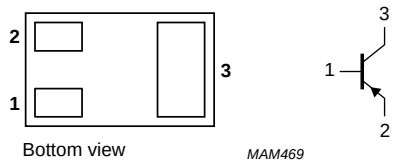


Fig.1 Simplified outline (SOT883) and symbol.

ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
BC857AM	–	Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.5 mm	SOT883
BC857BM			
BC857CM			

LIMITING VALUES

In accordance with the Absolute Maximum System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	−50	V
V_{CEO}	collector-emitter voltage	open base	–	−45	V
V_{EBO}	emitter-base voltage	open collector	–	−5	V
I_C	collector current (DC)		–	−100	mA
I_{CM}	peak collector current		–	−200	mA
I_{BM}	peak base current		–	−100	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C			
		note 1	–	250	mW
		note 2	–	430	mW
T_{stg}	storage temperature		−65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	operating ambient temperature		−65	+150	°C

Notes

1. Refer to SOT883 standard mounting conditions (footprint), FR4 with 60 μm copper strip line.
2. Device mounted on a FR4 printed-circuit board, single-sided copper, mounting pad for collector 1 cm^2.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air		
		note 1	500	K/W
		note 2	290	K/W

Notes

1. Refer to SOT883 standard mounting conditions (footprint), FR4 with 60 μm copper strip line.
2. Device mounted on a FR4 printed-circuit board, single-sided copper, mounting pad for collector 1 cm^2.

CHARACTERISTICS

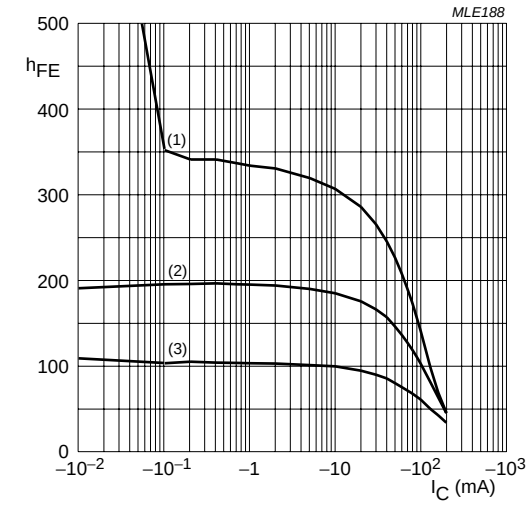
T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector-base cut-off current	V_{CB} = –30 V; I_E = 0	–	–15	nA
		V_{CB} = –30 V; I_E = 0; T_j = 150 °C	–	–5	μA
I_{EBO}	emitter-base cut-off current	V_{EB} = –5 V; I_C = 0	–	–100	nA
h_{FE}	DC current gain	V_{CE} = –5 V; I_C = –2 mA			
	BC857AM		125	250	
	BC857BM		220	475	
	BC857CM		420	800	
V_{BE}	base-emitter voltage	I_C = –2 mA; V_{CE} = –5 V	–600	–750	mV
		I_C = –10 mA; V_{CE} = –5 V	–	–820	mV
V_{CEsat}	collector-emitter saturation voltage	I_C = –10 mA; I_B = –0.5 mA	–	–200	mV
		I_C = –100 mA; I_B = –5 mA; note 1	–	–400	mV
C_c	collector capacitance	I_E = i_e = 0; V_{CB} = –10 V; f = 1 MHz	–	2.5	pF
f_T	transition frequency	V_{CE} = –5 V; I_C = –10 mA; f = 100 MHz	100	–	MHz
F	noise figure	I_C = –200 μA; V_{CE} = –5 V; R_S = 2 kΩ; f = 1 kHz; B = 200 Hz	–	10	dB

Note

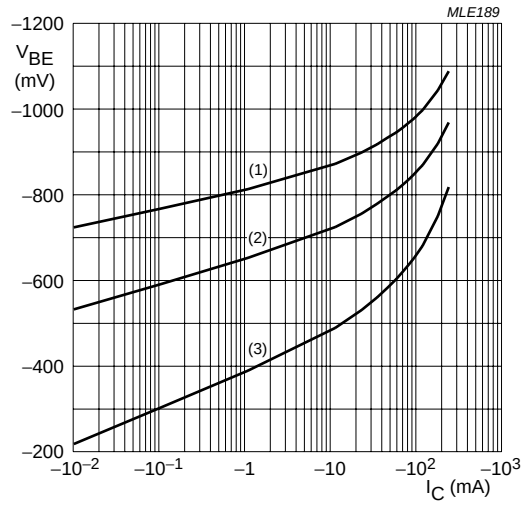
1. Pulse test: $t_p \leq 300$ μs; $\delta \leq 0.02$.

GRAPHICAL INFORMATION BC857AM



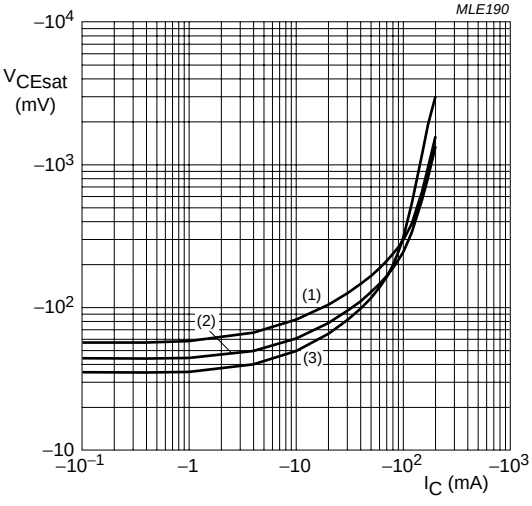
V_{CE} = −5 V.
(1) T_{amb} = 150 °C.
(2) T_{amb} = 25 °C.
(3) T_{amb} = −55 °C.

Fig.2 DC current gain; typical values.



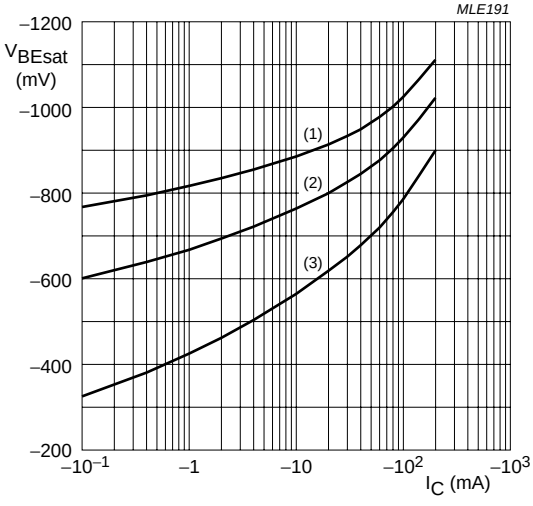
V_{CE} = −5 V.
(1) T_{amb} = −55 °C.
(2) T_{amb} = 25 °C.
(3) T_{amb} = 150 °C.

Fig.3 Base-emitter voltage as a function of collector current; typical values.



I_C/I_B = 20.
(1) T_{amb} = 150 °C.
(2) T_{amb} = 25 °C.
(3) T_{amb} = −55 °C.

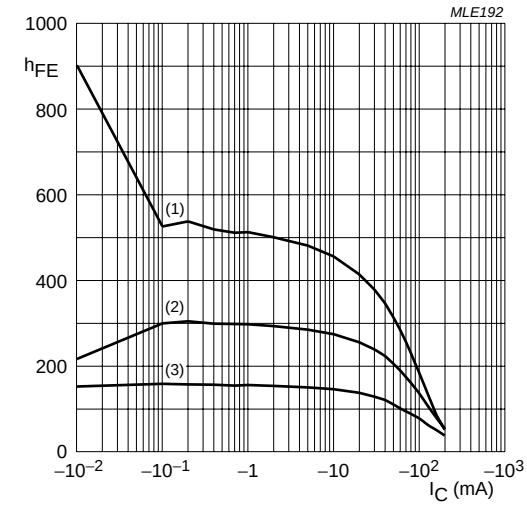
Fig.4 Collector-emitter saturation voltage as a function of collector current; typical values.



I_C/I_B = 20.
(1) T_{amb} = −55 °C.
(2) T_{amb} = 25 °C.
(3) T_{amb} = 150 °C.

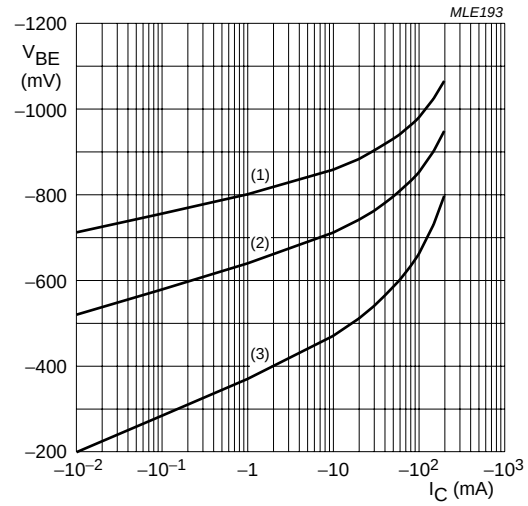
Fig.5 Base-emitter saturation voltage as a function of collector current; typical values.

GRAPHICAL INFORMATION BC857BM



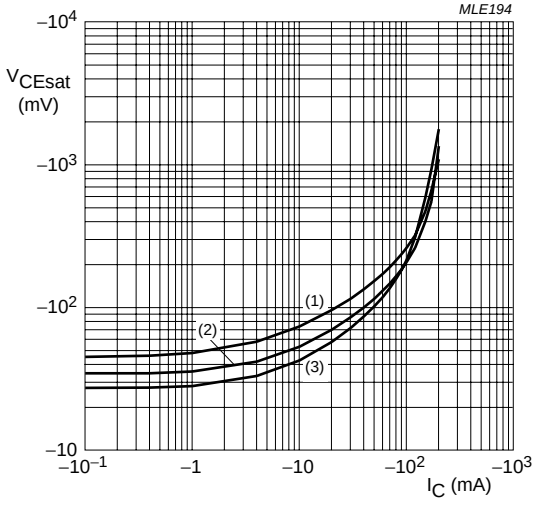
V_{CE} = −5 V.
(1) T_{amb} = 150 °C.
(2) T_{amb} = 25 °C.
(3) T_{amb} = −55 °C.

Fig.6 DC current gain; typical values.



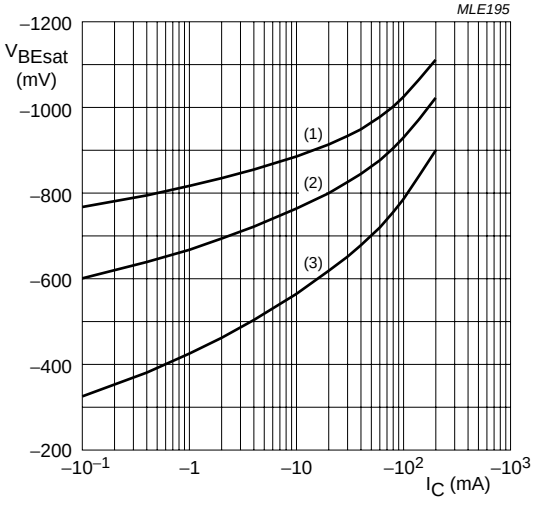
V_{CE} = −5 V.
(1) T_{amb} = −55 °C.
(2) T_{amb} = 25 °C.
(3) T_{amb} = 150 °C.

Fig.7 Base-emitter voltage as a function of collector current; typical values.



I_C/I_B = 20.
(1) T_{amb} = 150 °C.
(2) T_{amb} = 25 °C.
(3) T_{amb} = −55 °C.

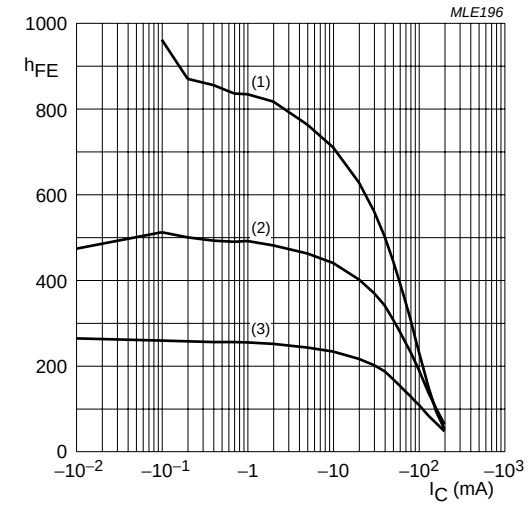
Fig.8 Collector-emitter saturation voltage as a function of collector current; typical values.



I_C/I_B = 20.
(1) T_{amb} = −55 °C.
(2) T_{amb} = 25 °C.
(3) T_{amb} = 150 °C.

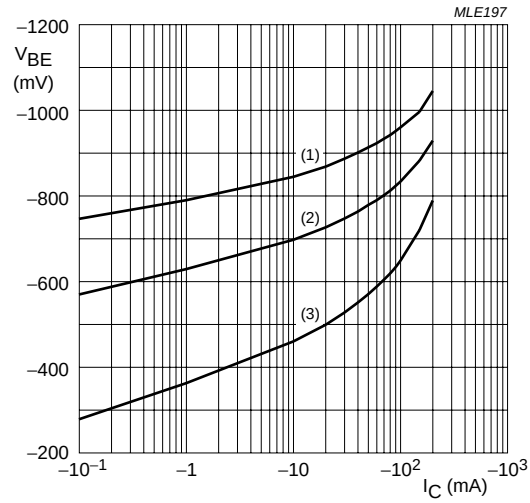
Fig.9 Base-emitter saturation voltage as a function of collector current; typical values.

GRAPHICAL INFORMATION BC857CM



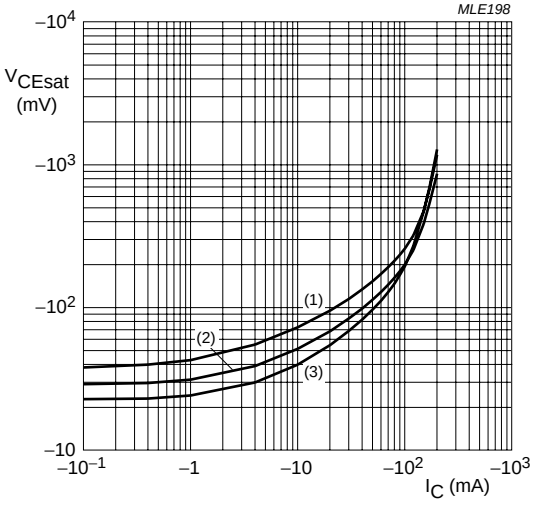
V_{CE} = −5 V.
(1) T_{amb} = 150 °C.
(2) T_{amb} = 25 °C.
(3) T_{amb} = −55 °C.

Fig.10 DC current gain; typical values.



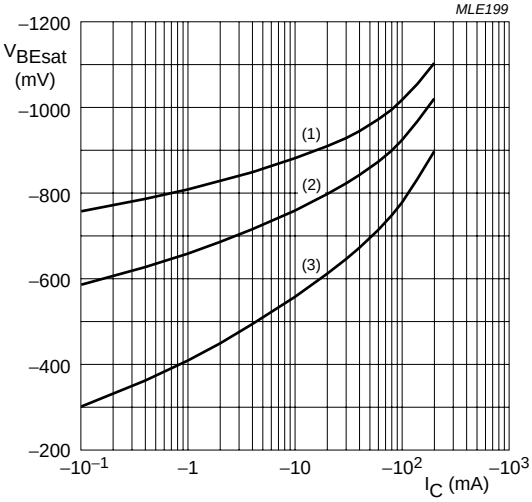
V_{CE} = −5 V.
(1) T_{amb} = −55 °C.
(2) T_{amb} = 25 °C.
(3) T_{amb} = 150 °C.

Fig.11 Base-emitter voltage as a function of collector current; typical values.



I_C/I_B = 20.
(1) T_{amb} = 150 °C.
(2) T_{amb} = 25 °C.
(3) T_{amb} = −55 °C.

Fig.12 Collector-emitter saturation voltage as a function of collector current; typical values.

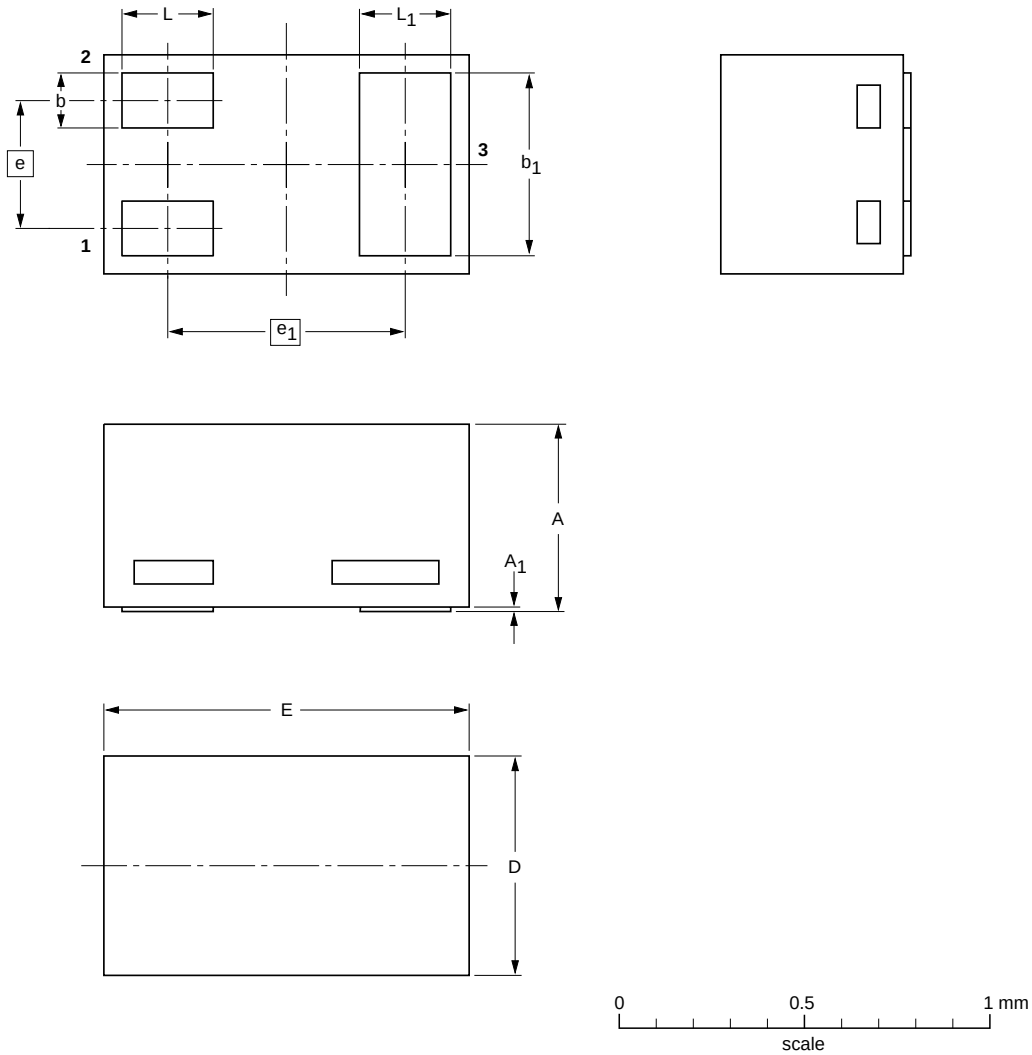


I_C/I_B = 20.
(1) T_{amb} = −55 °C.
(2) T_{amb} = 25 °C.
(3) T_{amb} = 150 °C.

Fig.13 Base-emitter saturation voltage as a function of collector current; typical values.

PACKAGE OUTLINE

Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.5 mm **SOT883**



DIMENSIONS (mm are the original dimensions)

UNIT	A(1)	A_1 max.	b	b_1	D	E	e	e_1	L	L_1
mm	0.50 0.46	0.03	0.20 0.12	0.55 0.47	0.62 0.55	1.02 0.95	0.35	0.65	0.30 0.22	0.30 0.22

Note

1. Including plating thickness

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT883			SC-101			~~03-02-05~~ 03-04-03

DATA SHEET STATUS

DOCUMENT STATUS[1]	PRODUCT STATUS[2]	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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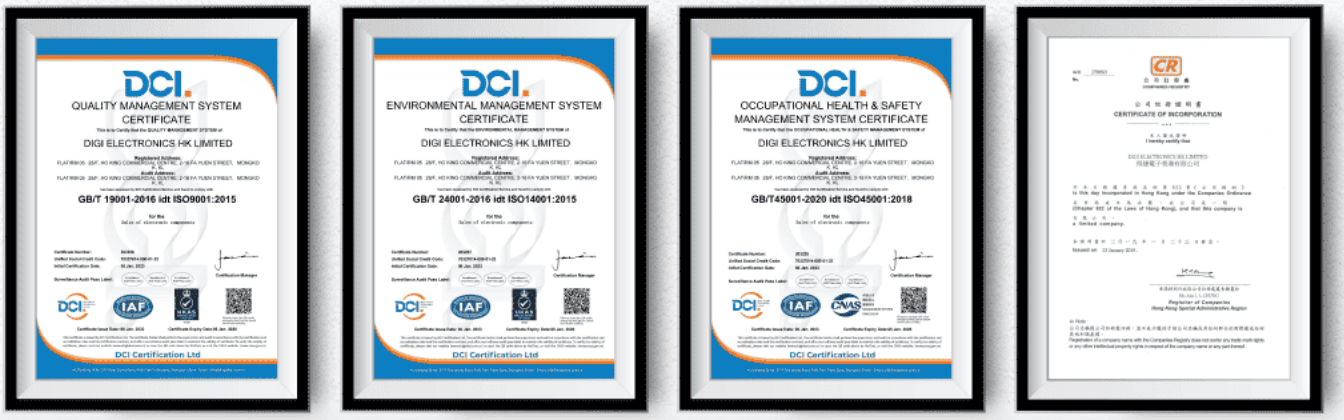

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